

C<sup>1</sup> wherein at least some of the melting of the upper portion of the polycrystalline silicon layer is performed as the amorphous silicon layer is melted.

---

C<sup>2</sup> 7. (Twice Amended) A method of forming a polycrystalline silicon layer, comprising:  
  
forming an amorphous silicon layer on a substrate;  
  
melting said amorphous silicon layer using a laser beam so as to form a polycrystalline silicon layer; and  
  
re-melting only an upper portion of said polycrystalline silicon layer using a laser beam so as to re-crystallize said upper portion,  
  
wherein at least some of said re-melting of said upper portion of said polycrystalline silicon layer is performed as said amorphous silicon layer is melted.

---

C<sup>3</sup> 18. (Amended) A method of forming a polycrystalline silicon layer, comprising:  
  
forming an amorphous silicon layer on a substrate;  
  
melting the amorphous silicon layer using a laser beam thereby forming the polycrystalline silicon layer using a mask; and  
  
melting only an upper portion of the polycrystalline silicon layer using the laser beam with the mask thereby recrystallizing the upper portion of the polycrystalline silicon layer,